

A fast, high-endurance and scalable non-volatile memory
Ta₂O₅^x/TaO₂^x bilayer structures

Nature Materials

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Citation Report

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5	Enhanced and reproducible X-ray emission in a low-energy plasma focus. <i>Europhysics Letters</i> , 2006, 73, 42-48.	0.7	18
6	Filamentary-switching model in RRAM for time, energy and scaling projections. , 2011, , .		39
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